

FEATURES

Power dissipation

$$P_{CM} : 1.25 \quad W \quad (T_{amb}=25^{\circ}C)$$

Collector current

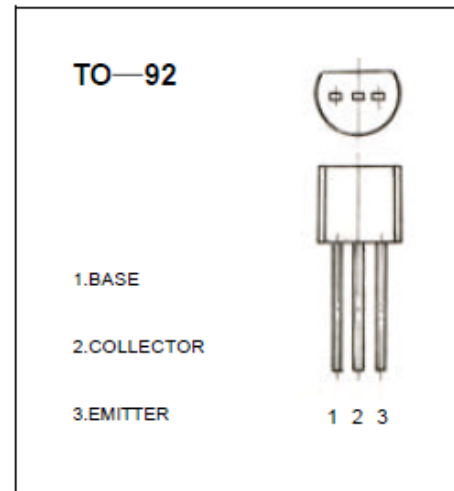
$$I_{CM} : 0.2 \quad A$$

Collector-base voltage

$$V_{(BR)CBO} : 600 \quad V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100 \mu A, I_E=0$	600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1 mA, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100 \mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=600 V, I_E=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6 V, I_C=0$			100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10 V, I_C=250 \mu A$	5			
	$h_{FE(2)}$	$V_{CE}=10 V, I_C=200 mA$	9		40	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200 mA, I_B=40 mA$			0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=200 mA, I_B=40 mA$			1.1	V
Transition frequency	f_T	$V_{CE}=10 V, I_C=100 mA$ $f=1 MHz$	5			MHz
Fall time	t_f	$I_C=1 A, I_{B1}=-I_{B2}=0.2 A$			0.5	μs
Storage time	t_s	$V_{CC}=100 V$			2.5	μs

CLASSIFICATION OF $h_{FE(2)}$

Rank						
Range	9-15	15-20	20-25	25-30	30-35	35-40